

Title (en)

METHOD FOR PRODUCING A SEMI-CONDUCTOR ARRANGEMENT AND THE USE OF AN ION BEAM ARRANGEMENT FOR CARRYING OUT SAID METHOD

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER HALBLEITERANORDNUNG UND VERWENDUNG EINER IONENSTRAHLANLAGE ZUR DURCHFÜHRUNG DES VERFAHRENS

Title (fr)

PROCEDE DE FABRICATION D'UN DISPOSITIF A SEMI-CONDUCTEUR ET UTILISATION D'UNE INSTALLATION A FAISCEAU IONIQUE POUR LA MISE EN OEUVRE DUDIT PROCEDE

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Application

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Abstract (en)

[origin: WO02080240A2] The invention relates to a lithographic method for removing a thin masking layer, particularly a Si₃N₄ layer on a side of a recess in a semi-conductor arrangement. According to the invention, an ion beam is orientated in an inclined manner at a certain angle towards the recess, enabling the thin masking layer to be removed in the regions exposed to the beams.

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